

## N-Channel 30-V (D-S) MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a, c</sup>	$Q_g$ (Typ.)
30	0.007 at $V_{GS} = 10$ V	70	60 nC
	0.009 at $V_{GS} = 4.5$ V	65	

### FEATURES

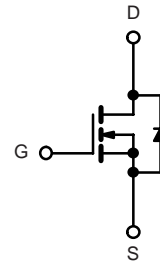
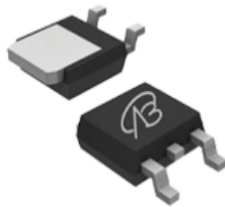
- TrenchFET<sup>®</sup> Power MOSFET
- 100 %  $R_g$  and UIS Tested

### APPLICATIONS

- Synchronous Rectification
- Power Supplies


**RoHS**  
 COMPLIANT

TO-252



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$ , unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	30	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175^\circ\text{C}$ )	$T_C = 25^\circ\text{C}$	$I_D$	70 <sup>a, c</sup>	A
	$T_C = 70^\circ\text{C}$		56 <sup>c</sup>	
	$T_A = 25^\circ\text{C}$		59 <sup>b</sup>	
	$T_A = 70^\circ\text{C}$		53 <sup>b</sup>	
Pulsed Drain Current		$I_{DM}$	210	mJ
Avalanche Current Pulse	L = 0.1 mH	$I_{AS}$	80	
Single Pulse Avalanche Energy		$E_{AS}$	310	
Continuous Source-Drain Diode Current	$T_C = 25^\circ\text{C}$	$I_S$	110 <sup>a, c</sup>	A
	$T_A = 25^\circ\text{C}$		2.6 <sup>b</sup>	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	$P_D$	312 <sup>a</sup>	W
	$T_C = 70^\circ\text{C}$		200	
	$T_A = 25^\circ\text{C}$		3.13 <sup>b</sup>	
	$T_A = 70^\circ\text{C}$		2.0 <sup>b</sup>	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to 150	$^\circ\text{C}$

### THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b</sup>	Steady State	$R_{thJA}$	32	40	$^\circ\text{C/W}$
Maximum Junction-to-Case	Steady State	$R_{thJC}$	0.33	0.4	

Notes:

a. Based on  $T_C = 25^\circ\text{C}$ .

b. Surface Mounted on 1" x 1" FR4 board.

c. Calculated based on maximum junction temperature. Package limitation current is 110 A.

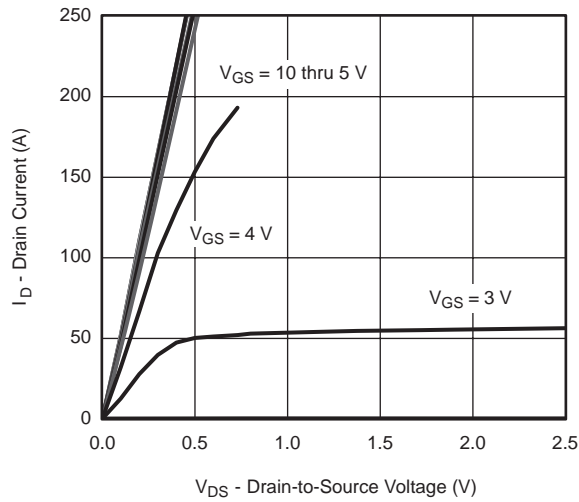
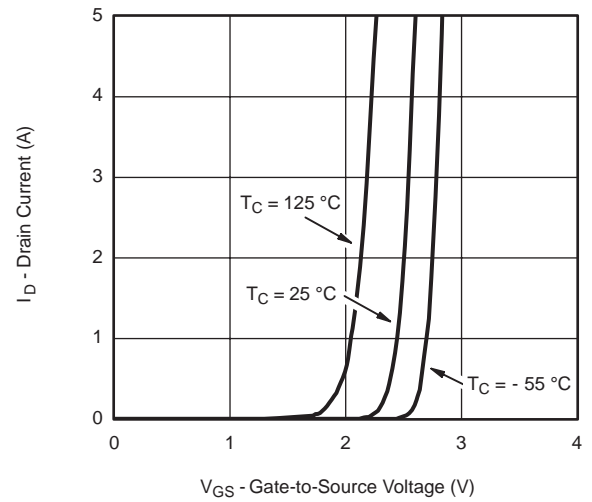
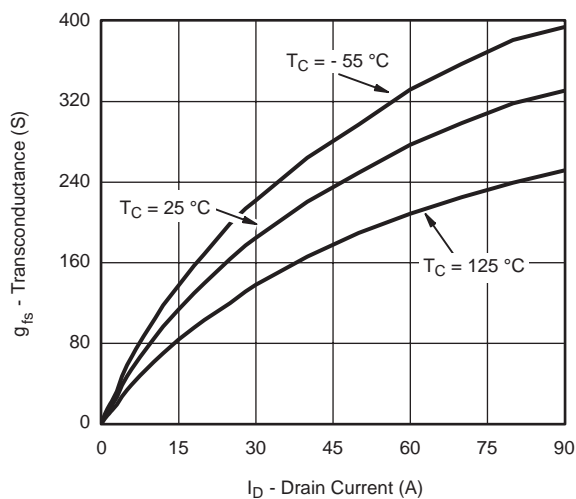
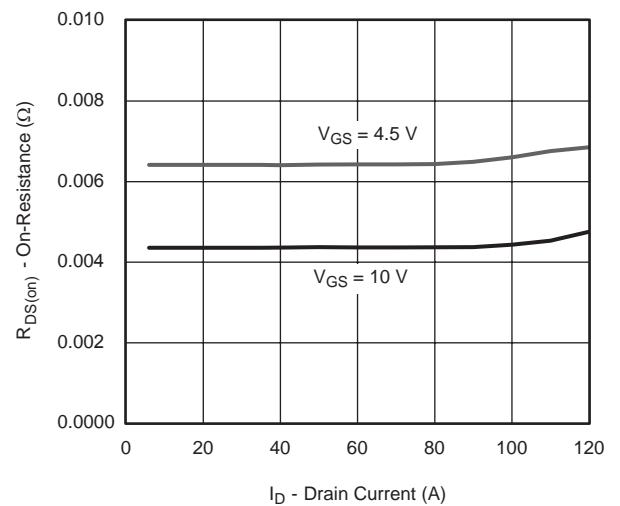
SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30			V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA		41		mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>			- 8		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.2		2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	120			A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A		0.007		Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A		0.009		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A		160		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, f = 1 MHz		2200		pF
Output Capacitance	C <sub>oss</sub>			550		
Reverse Transfer Capacitance	C <sub>rss</sub>			250		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		80	120	nC
Gate-Source Charge	Q <sub>gs</sub>			20		
Gate-Drain Charge	Q <sub>gd</sub>			12		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		0.85	1.3	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 20 V, R <sub>L</sub> = 1.0 Ω I <sub>D</sub> ≅ 20 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω		20	30	ns
Rise Time	t <sub>r</sub>			11	17	
Turn-Off Delay Time	t <sub>d(off)</sub>			77	115	
Fall Time	t <sub>f</sub>			10	15	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 20 V, R <sub>L</sub> = 1.0 Ω I <sub>D</sub> ≅ 20 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω		102	155	
Rise Time	t <sub>r</sub>			62	95	
Turn-Off Delay Time	t <sub>d(off)</sub>			180	270	
Fall Time	t <sub>f</sub>			60	90	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			70	A
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				210	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 20 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C		60	120	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			70	105	nC
Reverse Recovery Fall Time	t <sub>a</sub>			30		ns
Reverse Recovery Rise Time	t <sub>b</sub>			20		

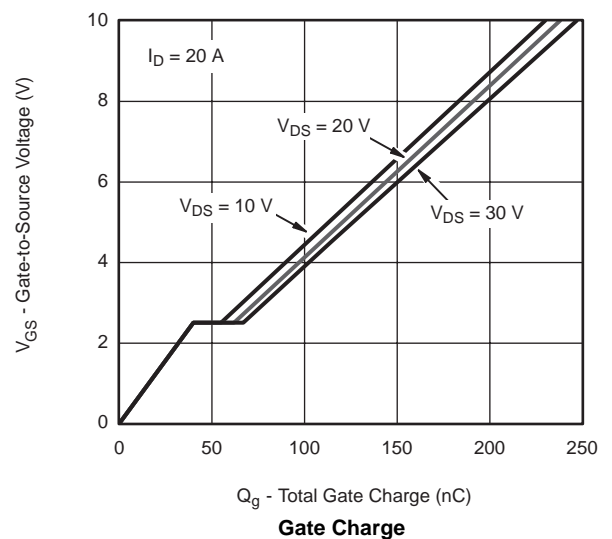
Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

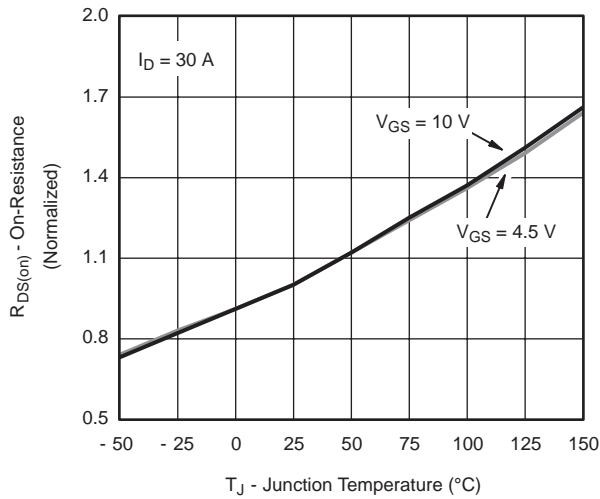
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

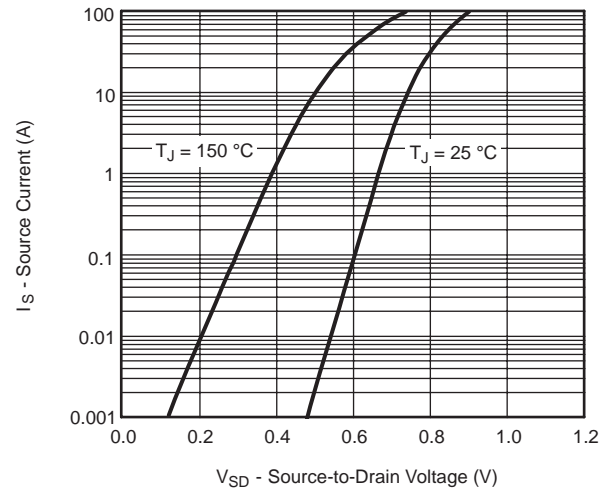
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

**Output Characteristics**

**Transfer Characteristics**

**Transconductance**

**On-Resistance vs. Drain Current**

**Capacitance**


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



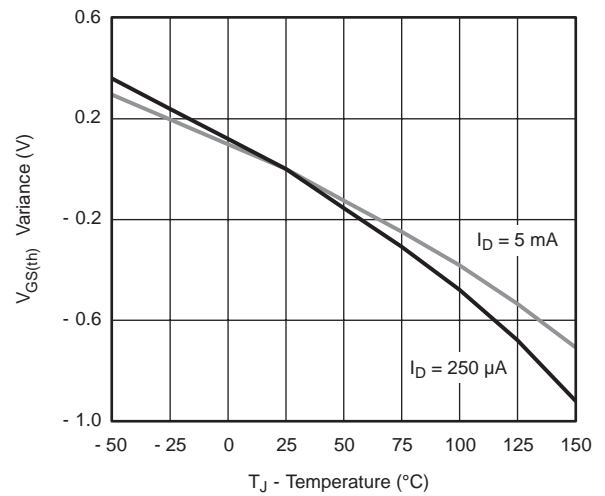
**On-Resistance vs. Junction Temperature**



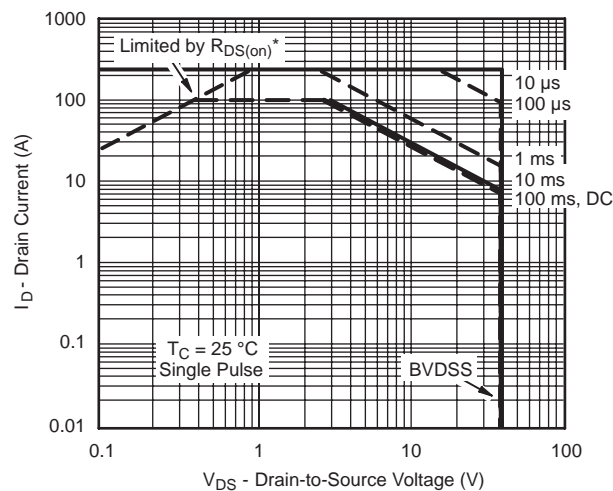
**Forward Diode Voltage vs. Temperature**



**On-Resistance vs. Gate-to-Source Voltage**



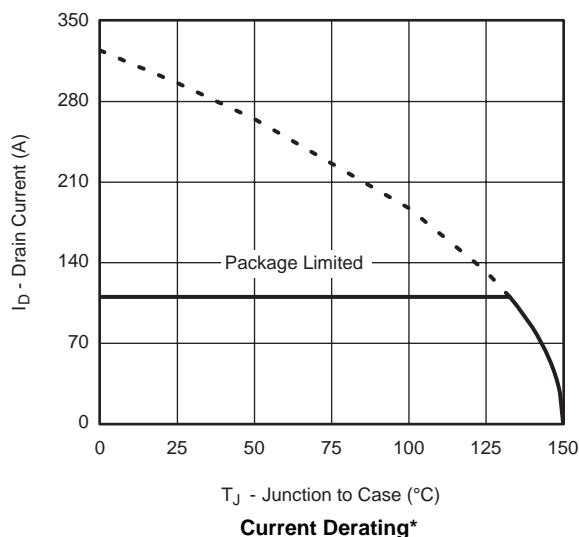
**Threshold Voltage**



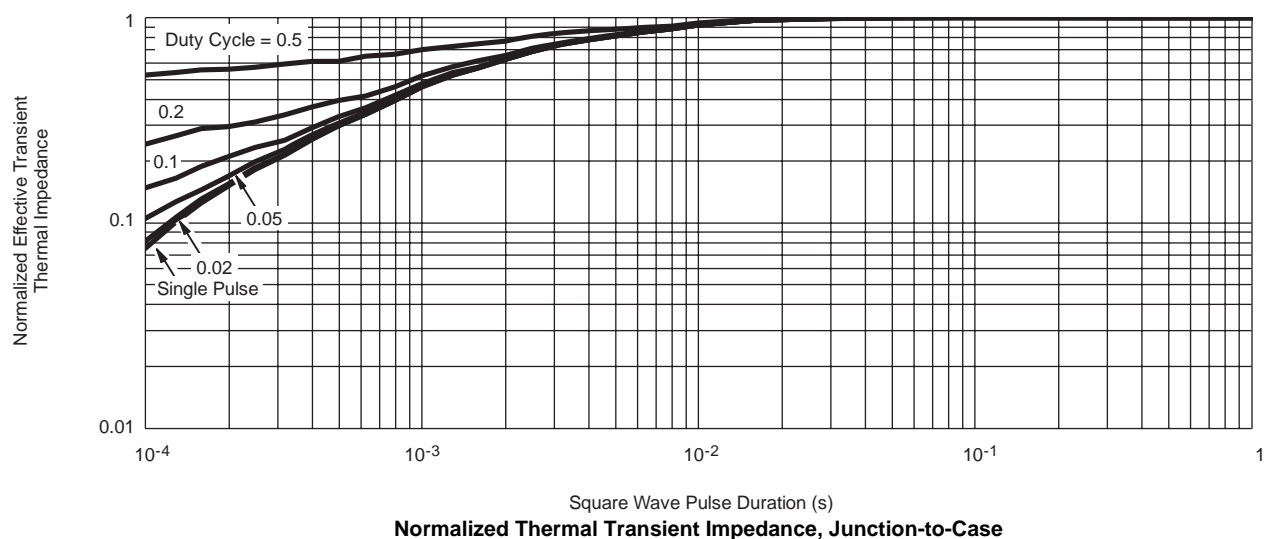
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**Safe Operating Area, Junction-to-Ambient**

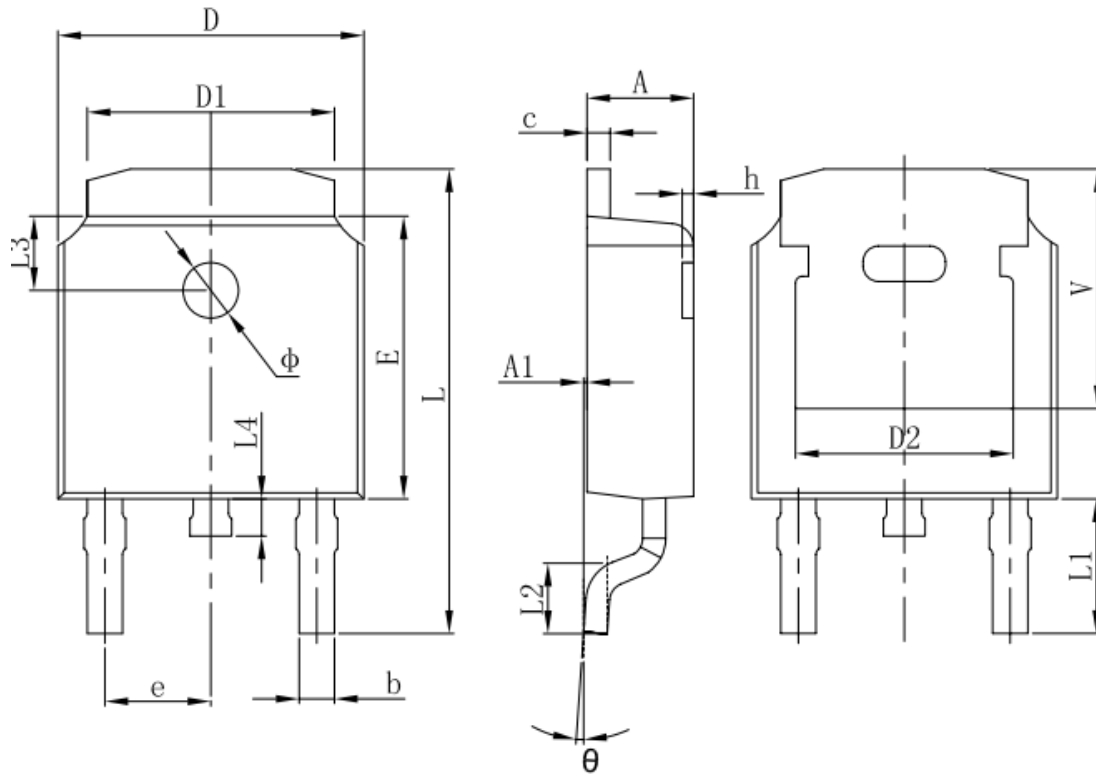
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150\text{ °C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

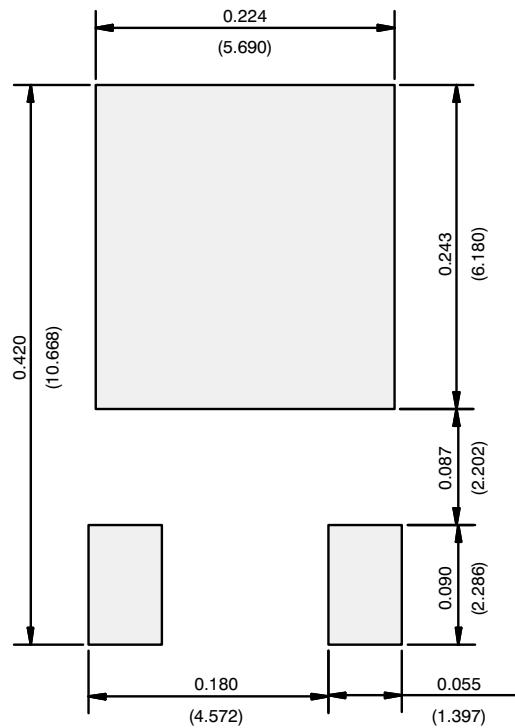


## TO252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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